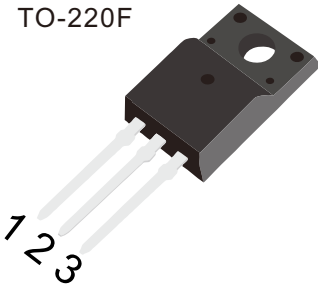


Main Product Characteristics

I_D	4A
V_{DSS}	600V
$P_D(T_C=25^\circ\text{C})$	30W
$R_{DS(ON)Typ}$	1.8Ω

Outline



1. Gate 2. Drain 3. Source

Features

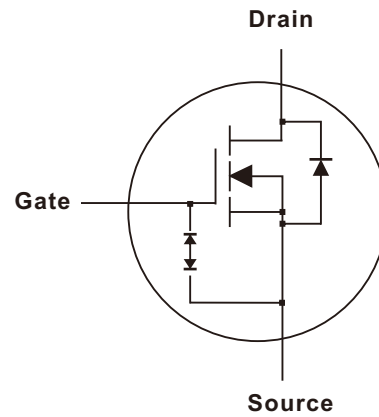
- Fast switching.
- ESD improved capability.
- Low gate charge. (Typical Data:14.5nC)
- Low reverse transfer capacitances. (Typical:8.5pF)
- 100% single pulse avalanche energy test.

Application

- Power switch circuit of adaptor and charger.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : JEDEC TO-220F molded plastic body over passivated chip
- Lead : Axial leads, solderable per MIL-STD-202, Method 208 guranteed.



Inner Equivalent principle Chart

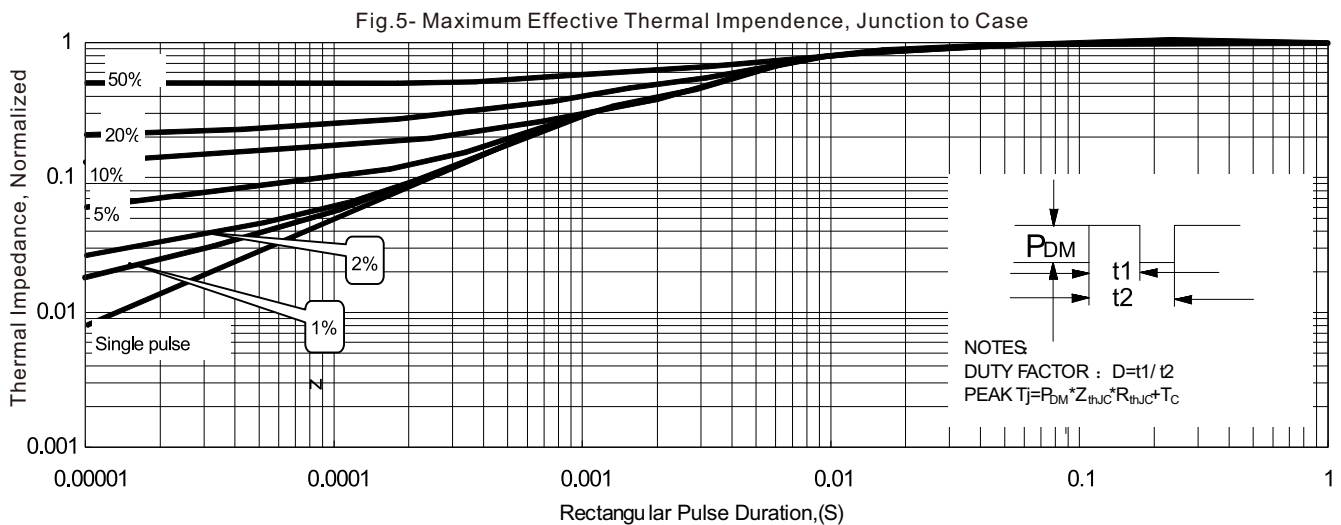
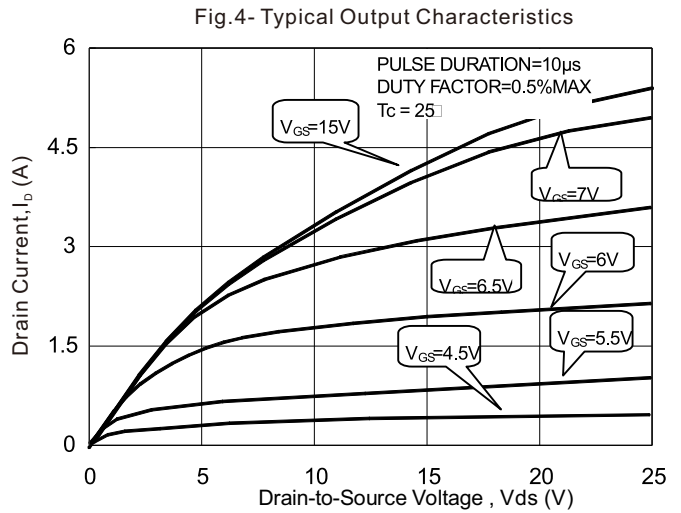
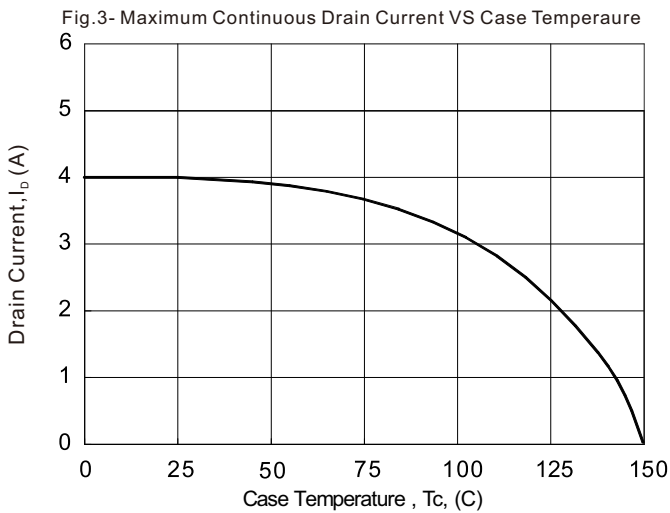
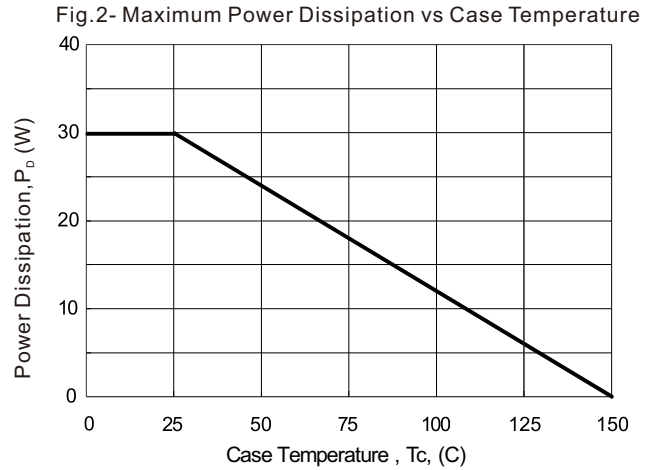
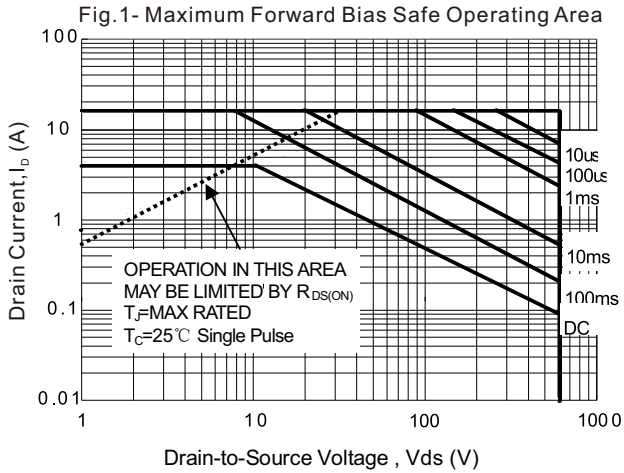
Absolute($T_C = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	CONDITIONS	Symbol	MHF04N60CT	UNIT
Drain to Source Voltage		V_{DSS}	600	V
Continuous Drain Current		I_D	4	A
Continuous Drain Current	$T_C = 100^\circ\text{C}$		3.2	
Pulsed Drain Current(Note:1)		I_{DM}	16	
Gate to Source Voltage		V_{GS}	±30	V
Single Pulse Avalanche Energy(Note:2)		E_{AS}	200	mJ
Avalanche Current(Note:1)		I_{AR}	2.5	A
Avalanche Energy, Repetitive (Note:1)		E_{AR}	30	mJ
Power Dissipation	Power Dissipation	P_D	30	W
	Derating factor above 25°C		0.24	W/°C
Peak Diode Recovery dv/dt(Note:3)		dv/dt	5.0	V/ns
Gate source ESD	HBM-C = 100pF, R = 1.5kΩ	$V_{ESD(G-S)}$	3000	V
Operating Junction and Storage Temperature Range		T_J, T_{STG}	150, -55 ~ +150	°C
Maximum temperature for soldering		T_L	300	°C

NOTE : 1.Repetitive rating; pulse width limited by maximum junction temperature.
 2.L=10.0mH, $I_0 = 6.3A$, Start $T_J = 25^\circ\text{C}$.
 3. $I_{SD} = 4A$, di/dt ≤ 100A/μs, $V_{DD} \leq BV_{DS}$, Start $T_J = 25^\circ\text{C}$.

■ Electrical characteristics($T_c = 25^\circ\text{C}$ unless otherwise specified)						
■ OFF Characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Drain to Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	V_{DSS}	600			V
Bvdss Temperature Coefficient	$I_D = 250\mu A$, Reference 25°C	$\Delta BV_{DSS} / \Delta T_J$		0.67		V/ $^\circ\text{C}$
Drain to Source Leakage Current	$V_{DS} = 600V, V_{GS} = 0V, T_a = 25^\circ\text{C}$	I_{DSS}			1	μA
	$V_{DS} = 480V, V_{GS} = 0V, T_a = 125^\circ\text{C}$				100	
Gate to Source Forward Leakage	$V_{GS} = +20V$	$I_{GSS(F)}$			10	
Gate to Source Reverse Leakage	$V_{GS} = -20V$	$I_{GSS(R)}$			-10	
■ ON Characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(th)}$	2.0		4.0	V
Drain-to-Source On-Resistance	$V_{GS} = 10V, I_D = 2A$	$R_{DS(on)}$		1.8	2.3	Ω
Pulse Width $t_p \leq 380\mu s, \delta \leq 2\%$						
■ Dynamic Characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward Trans conductance	$V_{DS} = 15V, I_D = 2A$	g_{fs}		3.5		S
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	C_{iss}		544		μF
Output Capacitance		C_{oss}		55		
Reverse Transfer Capacitance		C_{rss}		8.5		
■ Resistive Switching Characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Turn-on Delay Time	$I_D = 4A, V_{DD} = 300V, R_G = 4.7\Omega$	$t_{d(ON)}$		8.5		ns
Rise Time		t_r		6.5		
Turn-off Delay Time		$t_{d(OFF)}$		31		
Fail Time		t_f		8.5		
Total Gate Charge	$I_D = 4A, V_{DD} = 300V, V_{GS} = 10V$	Q_g		14.5		nC
Gate to Source Charge		Q_{gs}		2.8		
Gate to Drain ("Miller") Charge		Q_{gd}		6.3		
■ Source-Drain Diode Characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Continuous Source Current	Boby Diode	I_S			4	A
Maximum Pulse Current	Boby Diode	I_{SM}			16	
Diode Forward Voltage	$I_S = 4.0A, V_{GS} = 0V$	V_{SD}			1.5	V
Reverse recovery time	$I_S = 4A, T_J = 25^\circ\text{C}, di_f/dt = 100A/\mu s, V_{GS} = 0V$	t_{rr}		430		ns
Reverse recovery charge		Q_{rr}			1270	
Pulse Width $t_p \leq 300\mu s, \delta \leq 2\%$						
■ Thermal characteristics						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Thermal Resistance	Junction to Case	$R_{\theta JC}$		4.17		$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$		100		
■ Gate-source Zener Diode						
PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Gate-Source Breakdown Voltage	$I_{GS} = \pm 1\text{mA}(\text{open Drain})$	V_{GSO}	30			V

Rating and characteristic curves



Rating and characteristic curves

Fig.6- Maximum Peak Current Capability

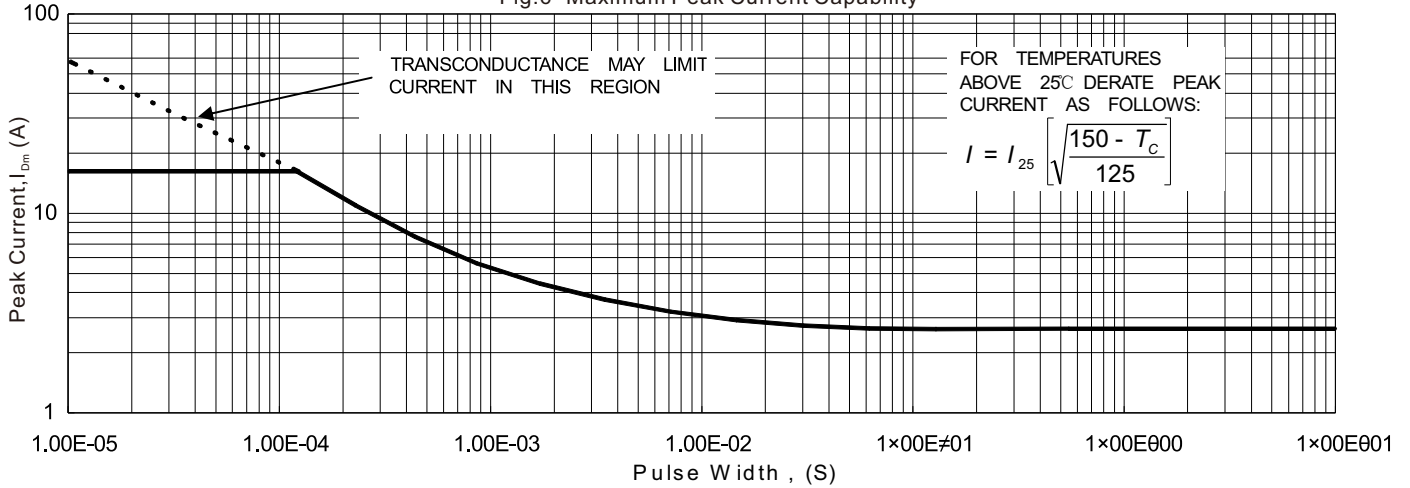


Fig.7- Typical Transfer Characteristics

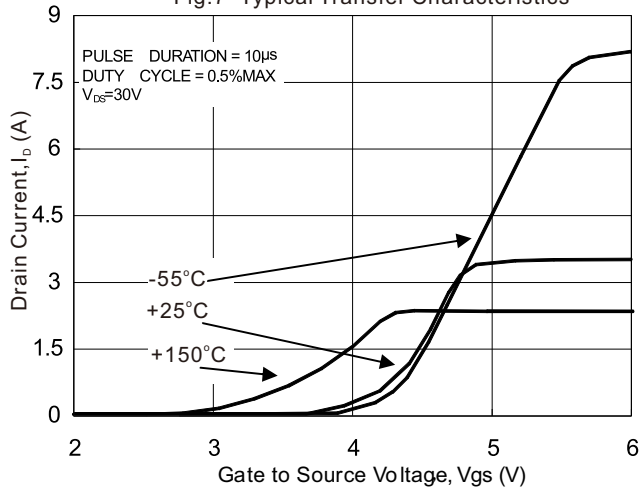


Fig.8- Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current

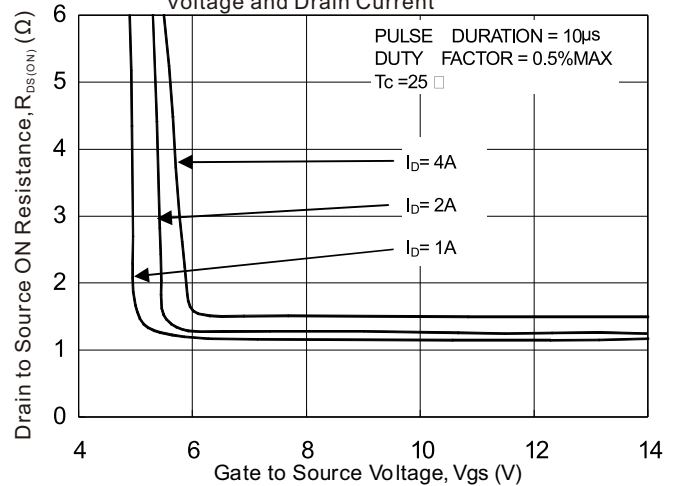


Fig.9- Typical Drain to Source ON resistance vs Drain Current

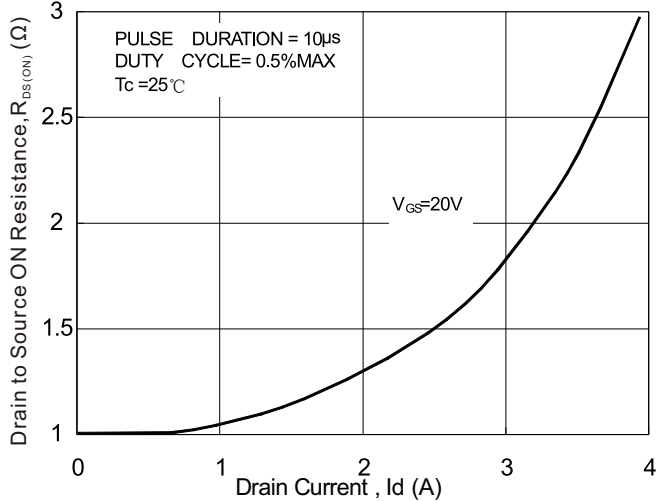
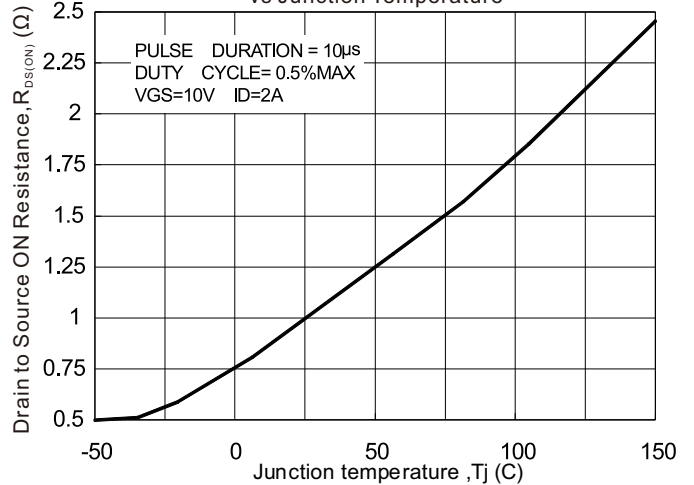


Fig.10- Typical Drain to Source ON resistance vs Junction Temperature



Rating and characteristic curves

Fig.11- Typical Threshold Voltage vs Junction Temperature

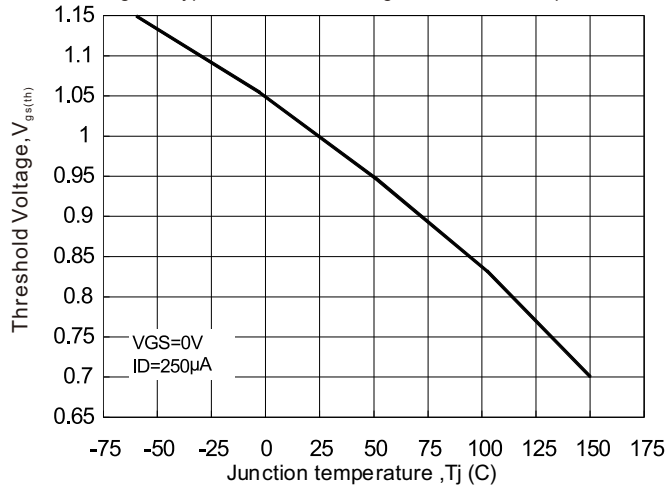


Fig.12- Typical Breakdown Voltage vs Junction Temperature

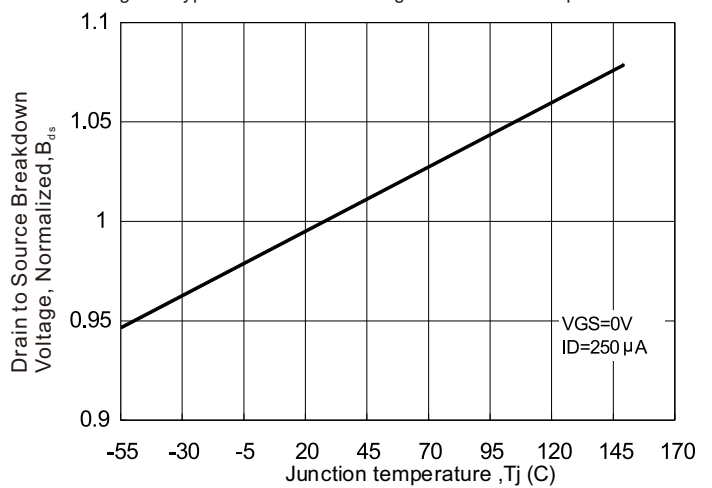


Fig.13- Typical Capacitance vs Drain to Source Voltage

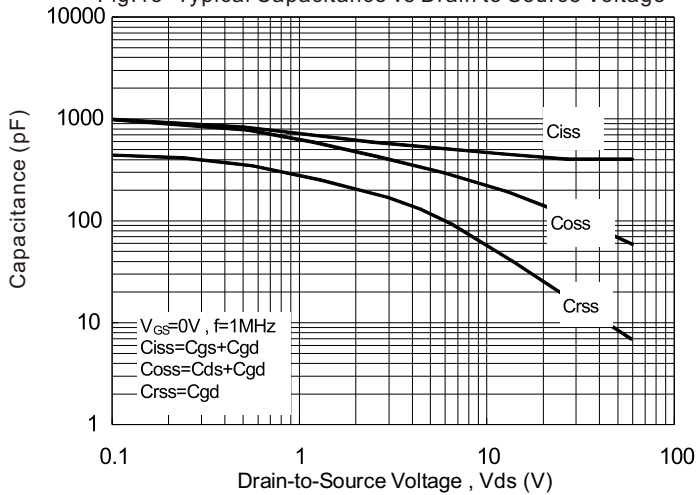


Fig.14- Typical Gate Charge vs Gate to Source Voltage

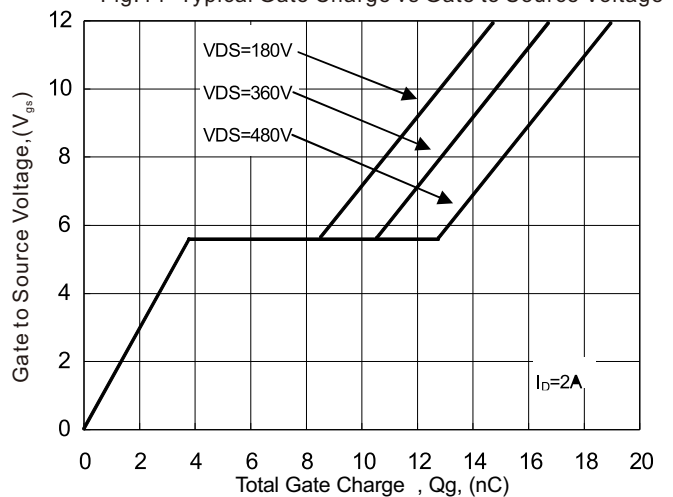


Fig.15- Typical Body Diode Transfer Characteristics

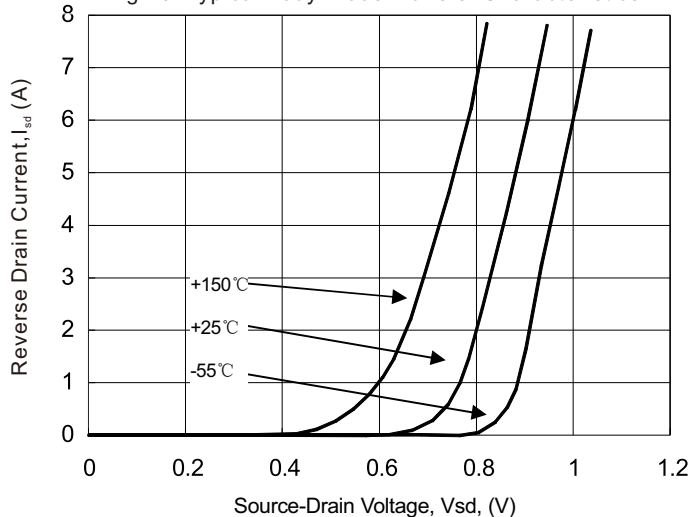
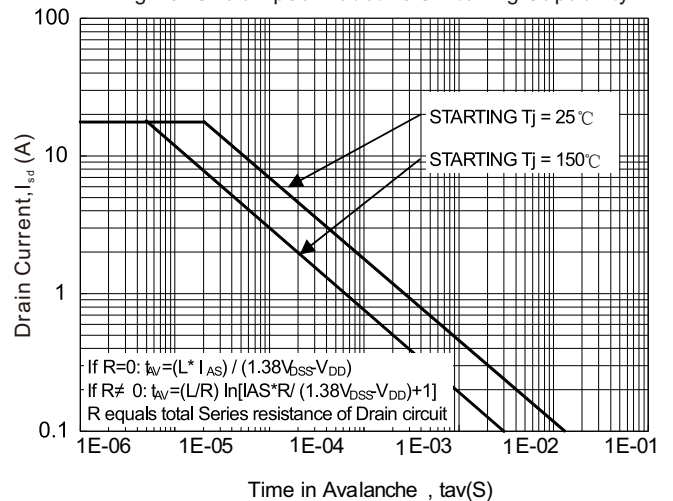


Fig.16- Unclamped Inductive Switching Capability



■ Test circuit and waveform

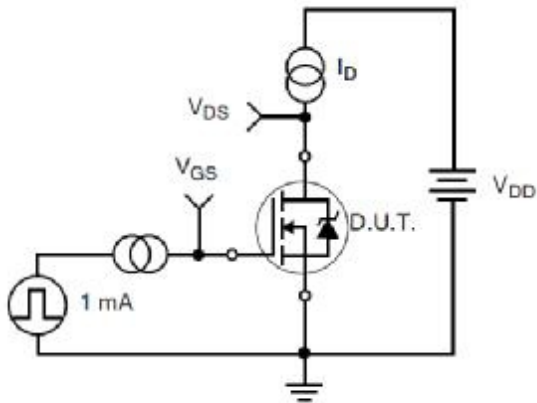


Figure 17. Gate Charge Test Circuit

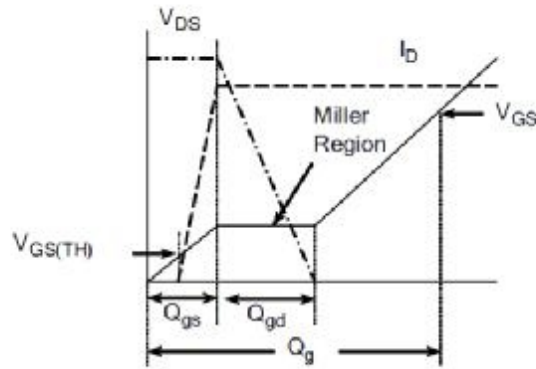


Figure 18. Gate Charge Waveform

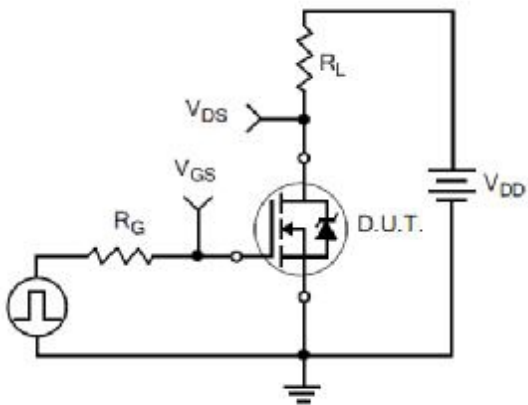


Figure 19. Resistive Switching Test Circuit

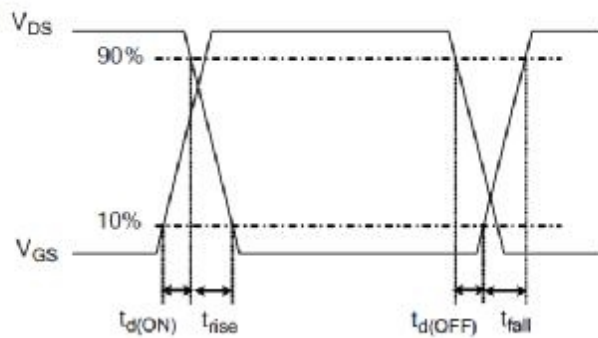


Figure 20. Resistive Switching Waveforms

■ Test circuit and waveform

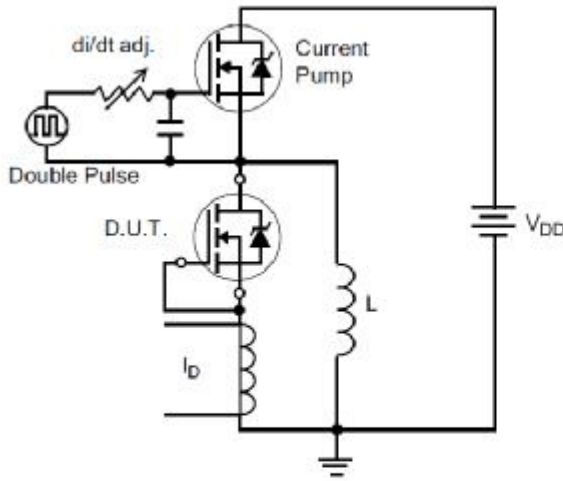


Figure 21. Diode Reverse Recovery Test Circuit

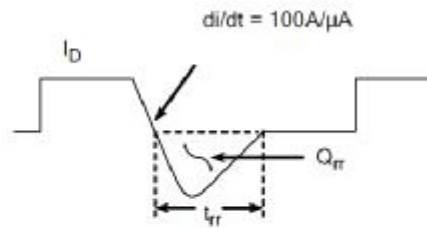


Figure 22. Diode Reverse Recovery Waveform

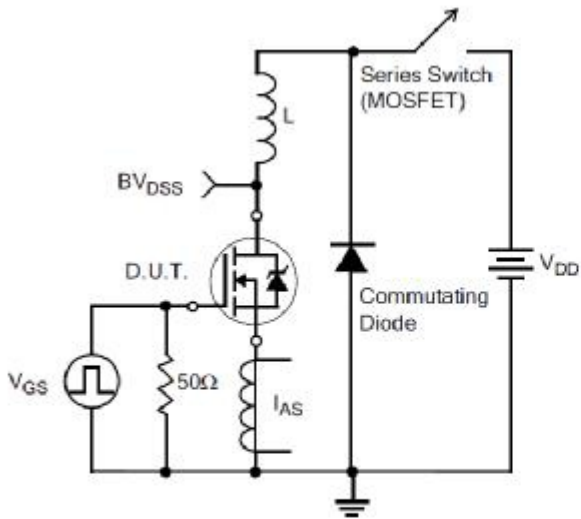


Figure 23. Unclamped Inductive Switching Test Circuit

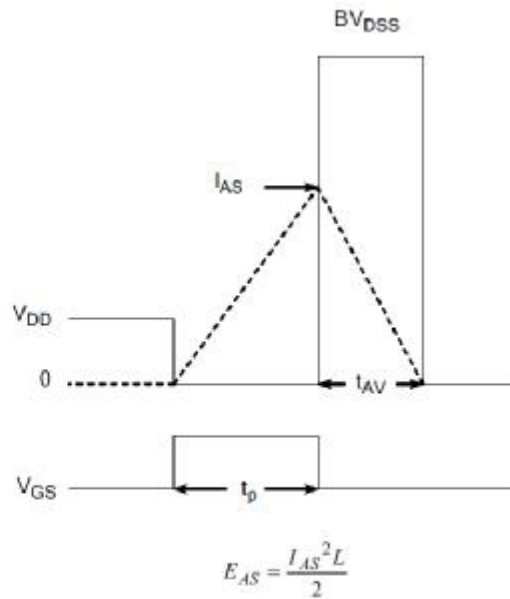
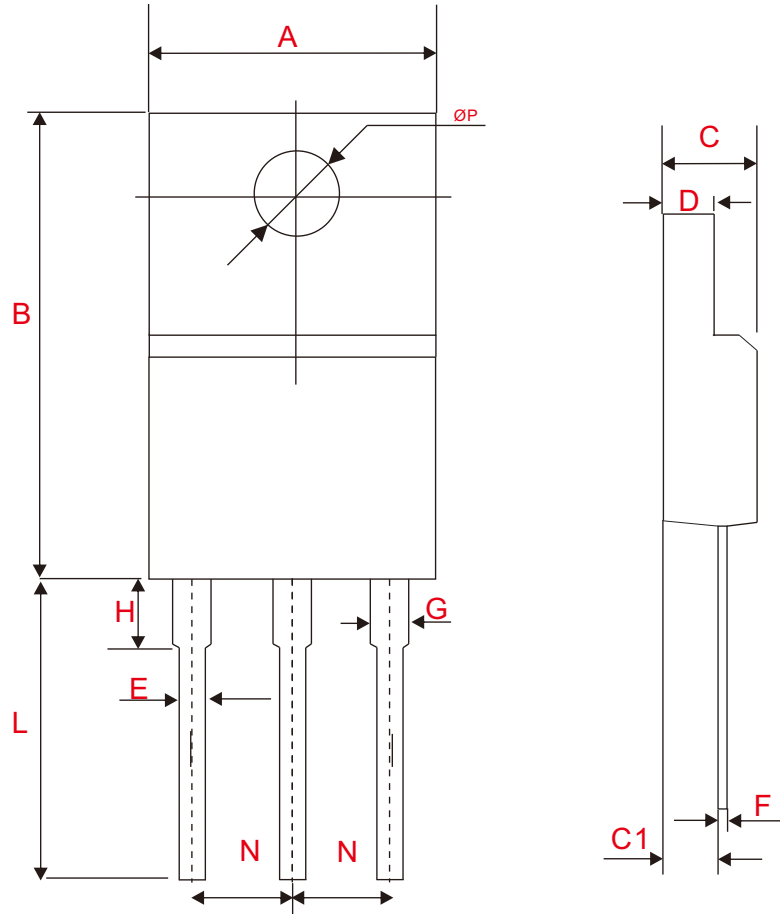


Figure 24. Unclamped Inductive Switching Waveforms

■ Package Information



Item	Values (mm)	
	Min	Max
A	9.60	10.40
B	15.40	16.20
C	4.40	4.90
C1	2.10	2.60
D	2.50	2.90
E	0.70	0.90
F	0.35	0.55
G	1.12	1.42
H	3.40	3.80
L	12.00	14.00
N	2.34	2.74
ØP	3.00	3.30

TO-220F Package

The name and content of poisonous and harmful material in products

Parts Name	Hazardous Substance					
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE
Limit	≤ 0.1%	≤ 0.1%	≤ 0.01%	≤ 0.1%	≤ 0.1%	≤ 0.1%
Lead Frame	○	○	○	○	○	○
Molding Compound	○	○	○	○	○	○
Chip	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○
Solder	×	○	○	○	○	○
Note	○: means the hazardous material is under the criterion of SJ/T11363-2006. ×: means the hazardous material exceeds the criterion of SJ/T11363-2006. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.					

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
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